



Initial Product/Process Change Notification

Document #: IPCN23751X1

Issue Date: 02 Mar 2021

Title of Change:	Update to IPCN23751X-Fabrication Site Transfer from BE2 (Belgium 6") to Fab10 (Pocatello, Id 8") for the Revision on Proposed First Ship, and Qual Completion Dates	
Proposed First Ship date:	15 Mar 2022 or earlier if approved by customer	
Contact Information:	Contact your local ON Semiconductor Sales Office or NoorArdila.Shaharuddin@onsemi.com	
PCN Samples Contact:	Contact your local ON Semiconductor Sales Office or PCN.samples@onsemi.com . Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.	
Type of Notification:	This is an Initial Product/Process Change Notification (IPCN) sent to customers. An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change. In case of questions, contact PCN.Support@onsemi.com	
Marking of Parts/ Traceability of Change:	Affected parts with this changing will be identified by the date code	
Change Category:	Wafer Fab Change	
Change Sub-Category(s):	Manufacturing Site Transfer, Manufacturing Process Change	
Sites Affected:		
ON Semiconductor Sites	External Foundry/Subcon Sites	
ON Semiconductor Oudenaarde, Belgium	None	
ON Semiconductor Pocatello Idaho, United States		
Description and Purpose:		
This is an update to IPCN23751X to inform customers on the correct First Ship Date, and Qual Completion Date. The change will not be affecting the form, fit, function, quality & reliability of the product.		
	Before Change Description	After Change Description
Bond Wire	Au wire	Au wire Cu wire (part numbers with ** in Qualification Vehicle list only)
Other Changes	Wafer manufacturing in Fab2 BE2	Wafer manufacturing in Fab10 USU
There is no product marking change as a result of this change.		

**Qualification Plan:****QV1 DEVICE NAME:** SESD7L5.0DT5G**RMS:** TBC**PACKAGE:** SOT-723-3

Test	Specification	Condition	Interval
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta = Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

QV2 DEVICE NAME: SESD9L5.0ST5G**RMS:** TBC**PACKAGE:** SOD923

Test	Specification	Condition	Interval
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta = Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

QV3 DEVICE NAME: NUP4114UPXV6T1G**RMS:** TBC**PACKAGE:** SOT-563-3

Test	Specification	Condition	Interval
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	1008 hrs
HTSL	JESD22-A103	Ta = Max rate storage temp for device = 150°C	1008 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

QV4 DEVICE NAME: SZCM1213A-04SO**RMS:** TBC**PACKAGE:** SC-74

Test	Specification	Condition	Interval
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta = Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

**QV5 DEVICE NAME: SZESD7008MUTAG****RMS: TBC****PACKAGE: 5.5x1.5 UDFN-18**

Test	Specification	Condition	Interval
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta = Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

QV6 DEVICE NAME: SZNUP4114HMR6T1G**RMS: TBC****PACKAGE: TSOP-6**

Test	Specification	Condition	Interval
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta = Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

QV7 DEVICE NAME: ESDR0502NMUTAG**RMS: TBC****PACKAGE: UDFN-6 1.2x1**

Test	Specification	Condition	Interval
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta = Max rate storage temp for device = 150°C	1008 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	96 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

Estimated date for qualification completion: 30 October 2021

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

Part Number	Qualification Vehicle
ESDR0502BT1G	QBS to SESD7L5.0DT5G (QV#1), SZCM1213A-04SO (QV#4)
ESD7L5.0DT5G	QBS to SESD7L5.0DT5G (QV#1), NUP4114UPXV6T1G (QV#3)
ESD7M5.0DT5G	QBS to SESD7L5.0DT5G (QV#1), NUP4114UPXV6T1G (QV#3)



Initial Product/Process Change Notification

Document #: IPCN23751X1

Issue Date: 02 Mar 2021

ESD7951ST5G	QBS to SED9L5.0ST5G (QV#2)
ESD9D5.0ST5G	QBS to SED9L5.0ST5G (QV#2)
ESD9L3.3ST5G	QBS to SED9L5.0ST5G (QV#2)
ESD9L5.0ST5G	QBS to SED9L5.0ST5G (QV#2)
ESD9M5.0ST5G	QBS to SED9L5.0ST5G (QV#2)
ESD9P5.0ST5G	QBS to SED9L5.0ST5G (QV#2)
ESD9R3.3ST5G	QBS to SED9L5.0ST5G (QV#2)
ESD7004MUTAG	QBS to SZEESD7008MUTAG (QV#5)
ESD7008MUTAG	QBS to SZEESD7008MUTAG (QV#5) **
ESD7016MUTAG	QBS to SZEESD7008MUTAG (QV#5) **
ESD7104MUTAG	QBS to SZEESD7008MUTAG (QV#5), ESDR0502NMUTAG (QV#7) **
ESDR0524PMUTAG	QBS to SZEESD7008MUTAG (QV#5) **
ESDR0524SMUTAG	QBS to SZEESD7008MUTAG (QV#5) **
MG2040MUTAG	QBS to SZEESD7008MUTAG (QV#5) **
NUP3112UPMUTAG	QBS to SZEESD7008MUTAG (QV#5)
ESDR0502NMUTAG	QV#7
SCM1293A-04SO	QBS to SZCM1213A-04SO (QV#4)
CM1293A-04SO	QBS to SZCM1213A-04SO (QV#4)
CM1213A-04SO	QBS to SZCM1213A-04SO (QV#4)
NUP4114UPXV6T2G	QBS to NUP4114UPXV6T1G (QV#3)
NUP4114UPXV6T1G	QV#3
NUP4114UCW1T2G	QBS to SZCM1213A-04SO (QV#4)
NUP4114UCLW1T2G	QBS to SZCM1213A-04SO (QV#4)
NUP2114UPXV5T1G	QBS to NUP4114UPXV6T1G (QV#3)
NUP4114HMR6T1G	QBS to SZNUP4114HMR6T1G (QV#6) **
NUP2114UCMR6T1G	QBS to SZNUP4114HMR6T1G (QV#6) **
NUP3115UPMUTAG	QBS to ESDR0502NMUTAG (QV#7)
ESDR0502NMUTBG	QBS to ESDR0502NMUTAG (QV#7)

Japanese translation of the notification starts here.
通知の日本語訳はここから始まります。

Note: *The Japanese version is for reference only. In case of any differences between the English and Japanese version, the English version shall control.*

注：日本語版は参照用です。英語版と日本語版の違いがある場合は、英語版が優先されます。



初回製品 / プロセス変更通知

文書番号# : IPCN23751X1

発行日: 02 Mar 2021

変更件名:	IPCN23751X の更新 - BE2 (ベルギー 6 インチ) から Fab10 (アイダホ州ポカテロ 8 インチ) へのウェハー製造拠点移管において初回出荷予定日と認定完了日の改訂
初回出荷予定日:	15 Mar 2022 またはお客様からの承認が得られた場合はそれ以前
連絡先情報:	現地のオン・セミコンダクター営業所または < NoorArdila.Shaharuddin@onsemi.com > にお問い合わせください。
サンプル:	現地のオン・セミコンダクター営業所または < PCN.Samples@onsemi.com > にお問い合わせください。 サンプルは、この変更の初回通知、初回 PCN の日付から 30 日以内に要求してください。 サンプル納入時は、依頼日、数量、特別梱包材/ラベル条件によって異なります。
通知種別:	これは、お客様宛の初回製品 / プロセス変更通知 (IPCN) です。IPCN は、近日中に実施される変更に関する事前通知であり、変更の詳細および影響を受けるデバイスについての一般情報が記載されます。また、暫定的な信頼性認証計画も記載されます。 最終的な認定データおよび特性データは最終製品 / プロセス変更通知 (FPCN) に含まれます。この IPCN は、変更実施から少なくとも 90 日前に発行される最終製品 / プロセス変更通知 (FPCN) に先だって通知されます。ご不明な点がありましたら、< PCN.Support@onsemi.com > にお問い合わせください。
部品のマーキング/変更のトレーサビリティ:	影響を受ける製品は日付コードで識別されます。
変更カテゴリ:	ウェハファブの変更
変更サブカテゴリ:	製造プロセスの変更, 製造拠点の移管
影響を受ける拠点:	
外部製造工場 / 下請業者拠点:	外部製造工場 / 下請業者拠点:
ON Semiconductor Oudenaarde, Belgium	なし
ON Semiconductor Pocatello Idaho, United States	

説明および目的:

これは、IPCN23751X の更新であり、正しい初回出荷予定日と認定完了日をお客様にお知らせするものです。
この変更は、製品の形状、適合性、機能、品質、および信頼性に影響を及ぼしません。

	変更前の表記	変更後の表記
ボンドワイヤ	Au ワイヤ	Au ワイヤ Cu ワイヤ (認定試験用ビークルの一覧に ** が付いている製品番号のみ)
その他の変更	Fab2 BE2 でウェハー製造	Fab10 USU でウェハー製造

今回の変更に伴う製品マーキングの変更はありません。



初回製品 / プロセス変更通知

文書番号 : IPCN23751X1

発行日 : 02 Mar 2021

認定計画:

デバイス名 : SESD7L5.0DT5G

RMS : TBC

パッケージ : SOT-723-3

テスト	規格	条件	間隔
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta =Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

デバイス名 : SESD9L5.0ST5G

RMS : TBC

パッケージ : SOD923

テスト	規格	条件	間隔
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta =Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

デバイス名 : NUP4114UPXV6T1G

RMS : TBC

パッケージ : SOT-563-3

テスト	規格	条件	間隔
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	1008 hrs
HTSL	JESD22-A103	Ta =Max rate storage temp for device = 150°C	1008 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

デバイス名 : SZCM1213A-04SO

RMS : TBC

パッケージ : SC-74

テスト	規格	条件	間隔
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta =Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	



初回製品 / プロセス変更通知

文書番号# : IPCN23751X1

発行日: 02 Mar 2021

デバイス名 : SZESD7008MUTAG

RMS : TBC

パッケージ : 5.5x1.5 UDFN-18

テスト	規格	条件	間隔
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta =Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

デバイス名 : SZNUP4114HMR6T1G

RMS : TBC

パッケージ : TSOP-6

テスト	規格	条件	間隔
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta =Max rate storage temp for device = 150°C	2016 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	192 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

デバイス名 : ESDR0502NMUTAG

RMS : TBC

パッケージ : UDFN-6 1.2x1

テスト	規格	条件	間隔
HTRB	JESD22-A108	Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D	2016 hrs
HTSL	JESD22-A103	Ta =Max rate storage temp for device = 150°C	1008 hrs
TC	JESD22-A104	Temp = -65°C to +150°C; for 1000 cycles	1000 cyc
HAST	JESD22-A110	Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max	96 hrs
uHAST	JESD22-A118	Temp = 130°C, RH=85%, ~ 18.8 psig	96 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245°C or 260°C (pkg dependant)	
RSH	JESD22- B106	Ta=265°C 10 sec dwell B106	

認定完了予定日 30 October 2021

影響を受ける部品の一覧:

注: 部品一覧には標準部品番号 (既製品) のみが記載されています。本 PCN の影響を受けるカスタム部品番号は、PCN メールで提供される顧客個別の付録、または PCN カスタマイズポータルに記載されています。

部品番号	認定試験用ピークル
ESDR0502BT1G	QBS to SESD7L5.0DT5G (QV#1), SZCM1213A-04SO (QV#4)
ESD7L5.0DT5G	QBS to SESD7L5.0DT5G (QV#1), NUP4114UPXV6T1G (QV#3)



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ESD7M5.0DT5G	QBS to SESD7L5.0DT5G (QV#1), NUP4114UPXV6T1G (QV#3)
ESD7951ST5G	QBS to SESD9L5.0ST5G (QV#2)
ESD9D5.0ST5G	QBS to SESD9L5.0ST5G (QV#2)
ESD9L3.3ST5G	QBS to SESD9L5.0ST5G (QV#2)
ESD9L5.0ST5G	QBS to SESD9L5.0ST5G (QV#2)
ESD9M5.0ST5G	QBS to SESD9L5.0ST5G (QV#2)
ESD9P5.0ST5G	QBS to SESD9L5.0ST5G (QV#2)
ESD9R3.3ST5G	QBS to SESD9L5.0ST5G (QV#2)
ESD7004MUTAG	QBS to SZESD7008MUTAG (QV#5)
ESD7008MUTAG	QBS to SZESD7008MUTAG (QV#5) **
ESD7016MUTAG	QBS to SZESD7008MUTAG (QV#5) **
ESD7104MUTAG	QBS to SZESD7008MUTAG (QV#5), ESDR0502NMUTAG (QV#7) **
ESDR0524PMUTAG	QBS to SZESD7008MUTAG (QV#5) **
ESDR0524SMUTAG	QBS to SZESD7008MUTAG (QV#5) **
MG2040MUTAG	QBS to SZESD7008MUTAG (QV#5) **
NUP3112UPMUTAG	QBS to SZESD7008MUTAG (QV#5)
ESDR0502NMUTAG	QV#7
SCM1293A-04SO	QBS to SZCM1213A-04SO (QV#4)
CM1293A-04SO	QBS to SZCM1213A-04SO (QV#4)
CM1213A-04SO	QBS to SZCM1213A-04SO (QV#4)
NUP4114UPXV6T2G	QBS to NUP4114UPXV6T1G (QV#3)
NUP4114UPXV6T1G	QV#3
NUP4114UCW1T2G	QBS to SZCM1213A-04SO (QV#4)
NUP4114UCLW1T2G	QBS to SZCM1213A-04SO (QV#4)
NUP2114UPXV5T1G	QBS to NUP4114UPXV6T1G (QV#3)
NUP4114HMR6T1G	QBS to SZNUP4114HMR6T1G (QV#6) **
NUP2114UCMR6T1G	QBS to SZNUP4114HMR6T1G (QV#6) **
NUP3115UPMUTAG	QBS to ESDR0502NMUTAG (QV#7)
ESDR0502NMUTBG	QBS to ESDR0502NMUTAG (QV#7)